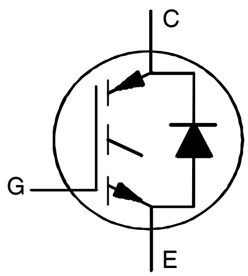
International
IOR Rectifier

AUTOMOTIVE GRADE

AUIRGP4063D
AUIRGP4063D-E

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



n-channel

V_{CES} = 600V

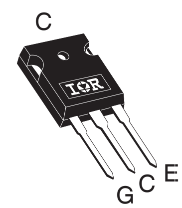
I_C = 60A, T_C = 100°C

$t_{SC} \geq$ 5µs, $T_{J(max)}$ = 175°C

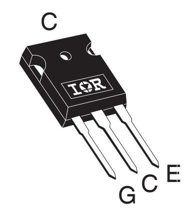
$V_{CE(on)}$ typ. = 1.6V

Features

- Low $V_{CE\ (ON)}$ Trench IGBT Technology
- Low switching losses
- Maximum Junction temperature 175 °C
- 5 µS short circuit SOA
- Square RBSOA
- 100% of the parts tested for 4X rated current (I_{LM})
- Positive $V_{CE\ (ON)}$ Temperature co-efficient
- Ultra fast soft Recovery Co-Pak Diode
- Tight parameter distribution
- Lead Free Package



TO-247AC
AUIRGP4063D



TO-247AD
AUIRGP4063D-E

G	C	E
Gate	Collector	Emitter

Benefits

- High Efficiency in a wide range of applications
- Suitable for a wide range of switching frequencies due to Low $V_{CE\ (ON)}$ and Low Switching losses
- Rugged transient Performance for increased reliability
- Excellent Current sharing in parallel operation
- Low EMI

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRGP4063D	TO-247	Tube	25	AUIRGP4063D
AUIRGP4063D-E	TO-247	Tube	25	AUIRGP4063D-E

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	100	A
I_C @ T_C = 100°C	Continuous Collector Current	60	
I_{CM}	Pulse Collector Current, V_{GE} = 15V	144	
I_{LM}	Clamped Inductive Load Current, V_{GE} = 20V ①	192	
I_F @ T_C = 25°C	Diode Continous Forward Current	82	
I_F @ T_C = 100°C	Diode Continous Forward Current	50	
I_{FM}	Diode Maximum Forward Current ③	192	
V_{GE}	Continuous Gate-to-Emitter Voltage	±20	V
	Transient Gate-to-Emitter Voltage	±30	
P_D @ T_C = 25°C	Maximum Power Dissipation	330	W
P_D @ T_C = 100°C	Maximum Power Dissipation	170	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf·in (1.1 N·m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT)	—	—	0.45	°C/W
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode)	—	—	0.92	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	—	80	—	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 150µA ④	CT6
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.30	—	V/°C	V_{GE} = 0V, I_C = 1mA (25°C-175°C)	CT6
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.6	1.9	V	I_C = 48A, V_{GE} = 15V, T_J = 25°C	5,6,7
		—	1.9	—		I_C = 48A, V_{GE} = 15V, T_J = 150°C	9,10,11
		—	2.0	—		I_C = 48A, V_{GE} = 15V, T_J = 175°C	
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	V_{CE} = V_{GE}, I_C = 1.4mA	9, 10,
$\Delta V_{GE(th)}/\Delta TJ$	Threshold Voltage temp. coefficient	—	-21	—	mV/°C	V_{CE} = V_{GE}, I_C = 1.0mA (25°C - 175°C)	11, 12
gfe	Forward Transconductance	—	32	—	S	V_{CE} = 50V, I_C = 48A, PW = 80µs	
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	150	µA	V_{GE} = 0V, V_{CE} = 600V	
		—	450	1000		V_{GE} = 0V, V_{CE} = 600V, T_J = 175°C	
V_{FM}	Diode Forward Voltage Drop	—	1.95	2.91	V	I_F = 48A	8
		—	1.45	—		I_F = 48A, T_J = 175°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig
Q_g	Total Gate Charge (turn-on)	—	95	140	nC	I_C = 48A	24
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	28	42		V_{GE} = 15V	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	35	53		V_{CC} = 400V	
E_{on}	Turn-On Switching Loss	—	625	1141	µJ	I_C = 48A, V_{CC} = 400V, V_{GE} = 15V	CT4
E_{off}	Turn-Off Switching Loss	—	1275	1481		R_G = 10Ω, L = 200µH, L_S = 150nH, T_J = 25°C	
E_{total}	Total Switching Loss	—	1900	2622		Energy losses include tail & diode reverse recovery	
$t_{d(on)}$	Turn-On delay time	—	60	78	ns	I_C = 48A, V_{CC} = 400V, V_{GE} = 15V	CT4
t_r	Rise time	—	40	56		R_G = 10Ω, L = 200µH, L_S = 150nH, T_J = 25°C	
$t_{d(off)}$	Turn-Off delay time	—	145	176			
t_f	Fall time	—	35	46			
E_{on}	Turn-On Switching Loss	—	1625	—	µJ	I_C = 48A, V_{CC} = 400V, V_{GE}=15V	13, 15
E_{off}	Turn-Off Switching Loss	—	1585	—		R_G=10Ω, L=200µH, L_S=150nH, T_J = 175°C ④	CT4
E_{total}	Total Switching Loss	—	3210	—		Energy losses include tail & diode reverse recovery	WF1, WF2
$t_{d(on)}$	Turn-On delay time	—	55	—	ns	I_C = 48A, V_{CC} = 400V, V_{GE} = 15V	14, 16
t_r	Rise time	—	45	—		R_G = 10Ω, L = 200µH, L_S = 150nH	CT4
$t_{d(off)}$	Turn-Off delay time	—	165	—		T_J = 175°C	WF1
t_f	Fall time	—	45	—			WF2
C_{ies}	Input Capacitance	—	3025	—	pF	V_{GE} = 0V	23
C_{oes}	Output Capacitance	—	245	—		V_{CC} = 30V	
C_{res}	Reverse Transfer Capacitance	—	90	—		f = 1.0Mhz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 175°C, I_C = 192A V_{CC} = 480V, Vp =600V Rg = 10Ω, V_{GE} = +15V to 0V	4 CT2
SCSOA	Short Circuit Safe Operating Area	5	—	—	µs	V_{CC} = 400V, Vp =600V Rg = 10Ω, V_{GE} = +15V to 0V	22, CT3 WF4
Erec	Reverse Recovery Energy of the Diode	—	845	—	µJ	T_J = 175°C	17, 18, 19
t_{rr}	Diode Reverse Recovery Time	—	115	—	ns	V_{CC} = 400V, I_F = 48A	20, 21
I_{rr}	Peak Reverse Recovery Current	—	40	—	A	V_{GE} = 15V, Rg = 10Ω, L =200µH, L_s = 150nH	WF3

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 200µH, R_G = 10Ω.

② This is only applied to TO-247AC package.

③ Pulse width limited by max. junction temperature.

④ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.

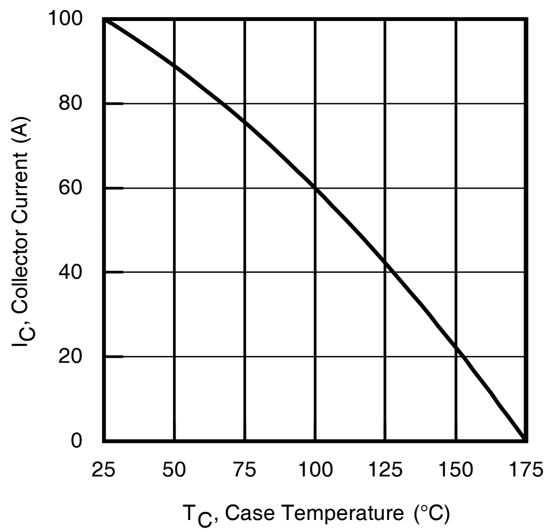


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

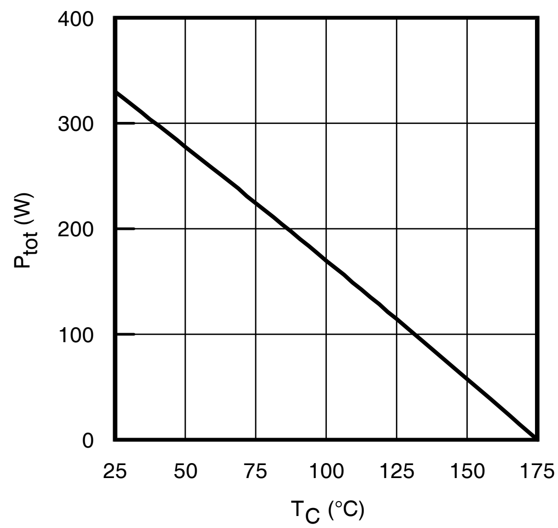


Fig. 2 - Power Dissipation vs. Case Temperature

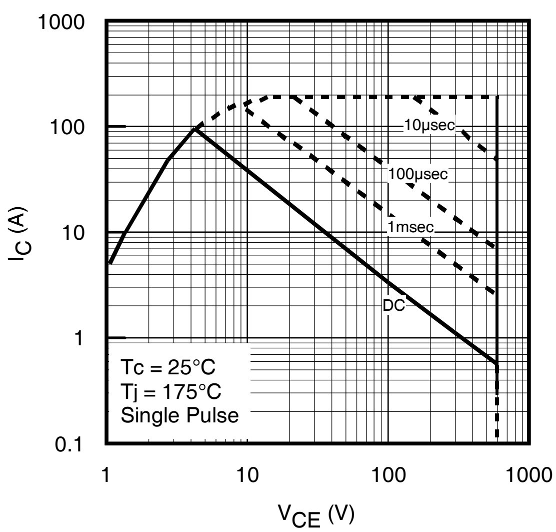


Fig. 3 - Forward SOA
T_C = 25°C, $T_J \leq$ 175°C; V_{GE} =15V

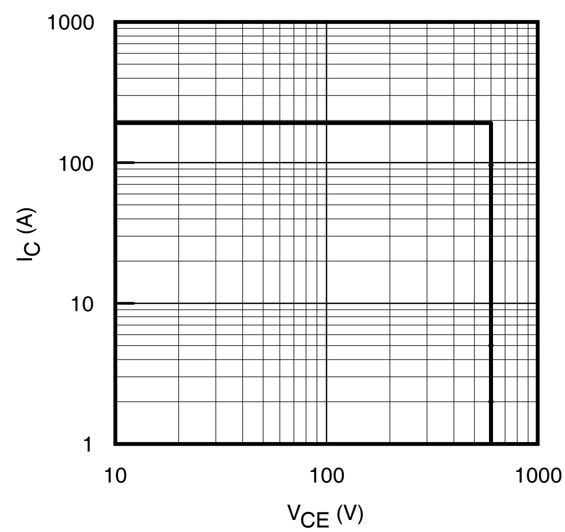


Fig. 4 - Reverse Bias SOA
T_J = 175°C; V_{GE} =15V

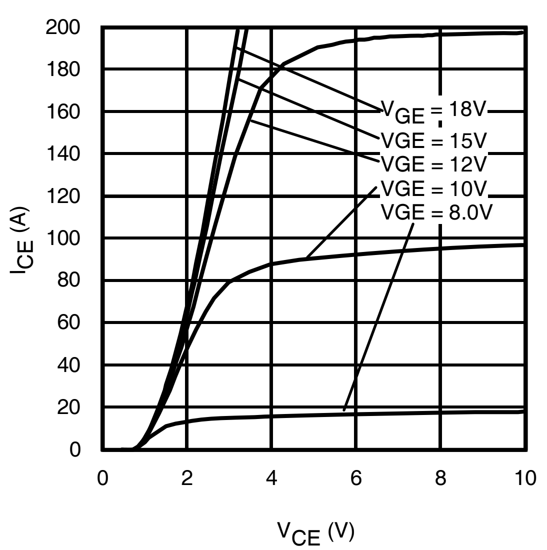


Fig. 5 - Typ. IGBT Output Characteristics
T_J = -40°C; tp = 80µs

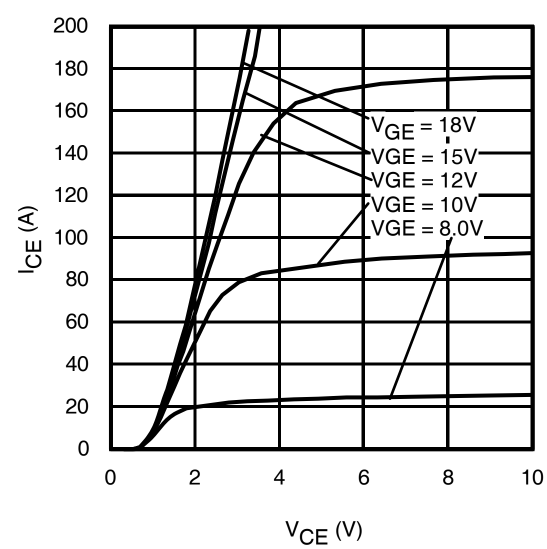


Fig. 6 - Typ. IGBT Output Characteristics
T_J = 25°C; tp = 80µs

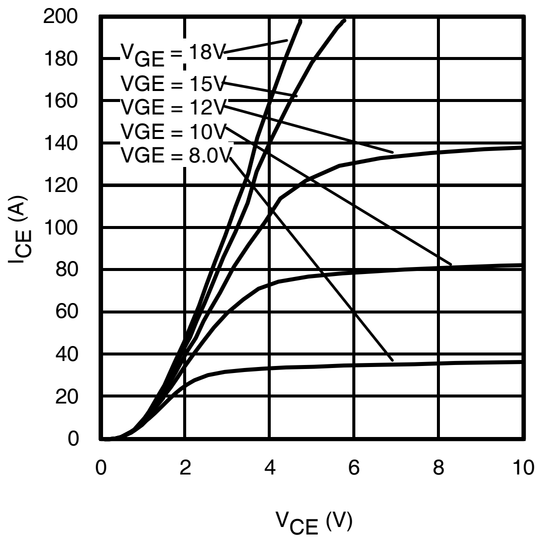


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 175°C; tp = 80µs

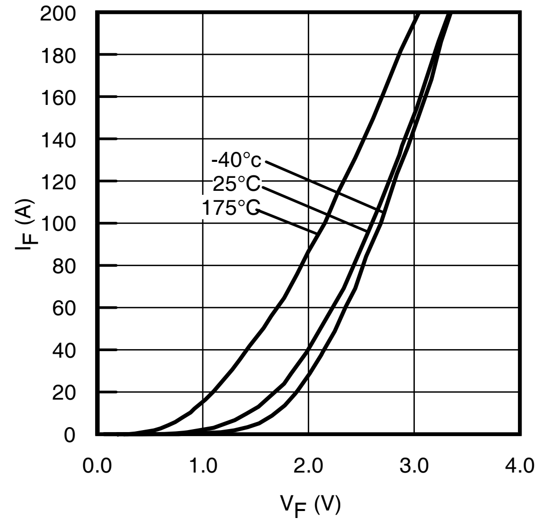


Fig. 8 - Typ. Diode Forward Characteristics
tp = 80µs

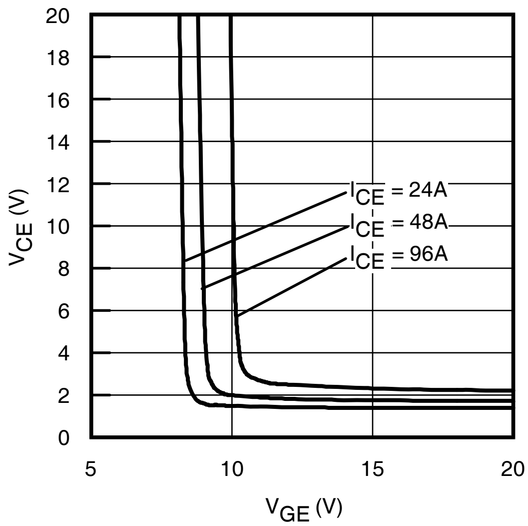


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

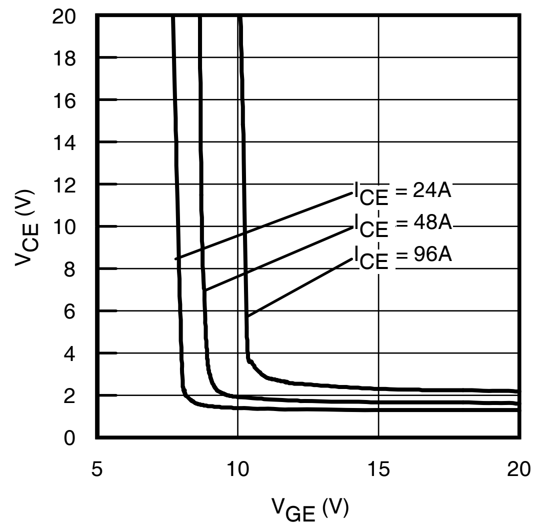


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

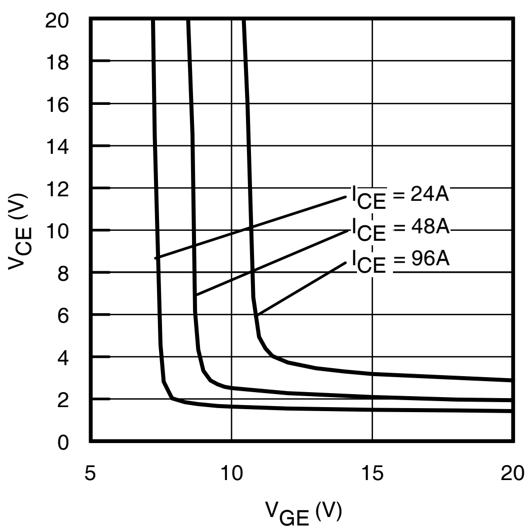


Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 175°C

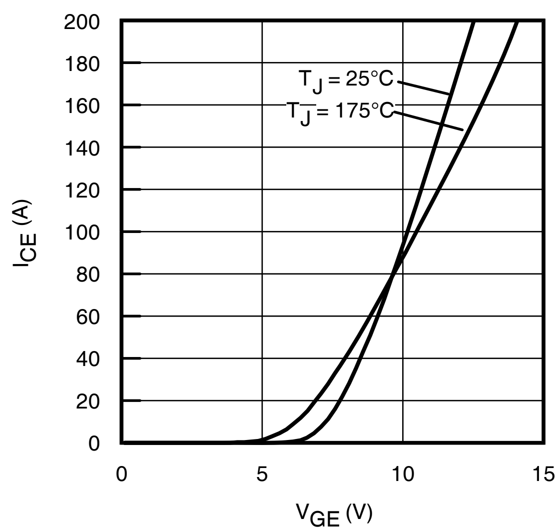


Fig. 12 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = 10µs

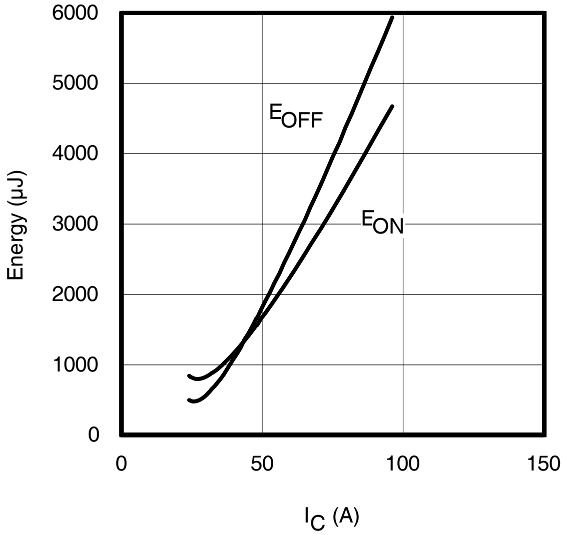


Fig. 13 - Typ. Energy Loss vs. I_C
$T_J = 175°C$; $L = 200µH$; $V_{CE} = 400V$, $R_G = 10Ω$; $V_{GE} = 15V$

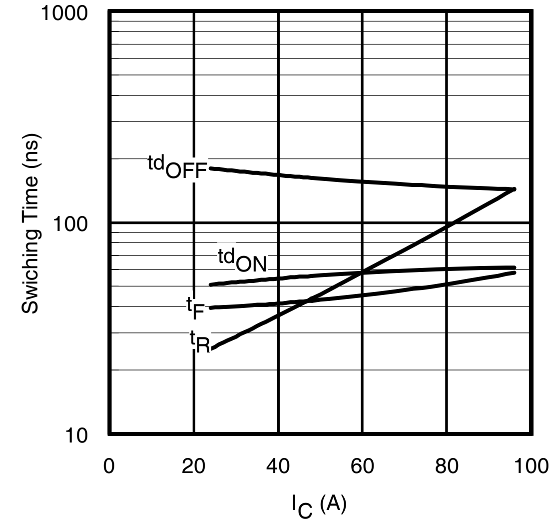


Fig. 14 - Typ. Switching Time vs. I_C
$T_J = 175°C$; $L = 200µH$; $V_{CE} = 400V$, $R_G = 10Ω$; $V_{GE} = 15V$

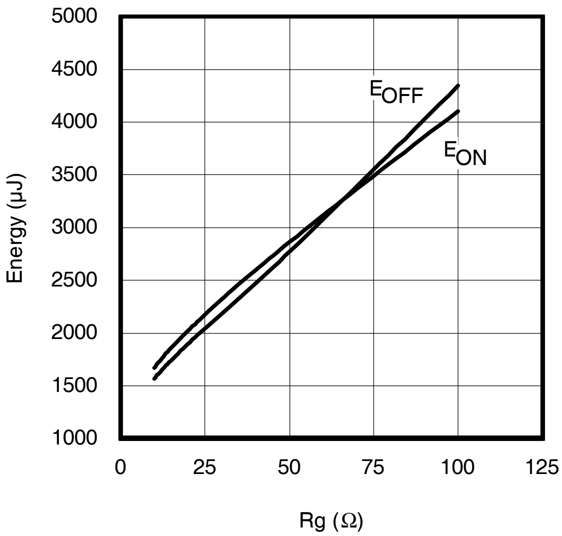


Fig. 15 - Typ. Energy Loss vs. R_G
$T_J = 175°C$; $L = 200µH$; $V_{CE} = 400V$, $I_{CE} = 48A$; $V_{GE} = 15V$

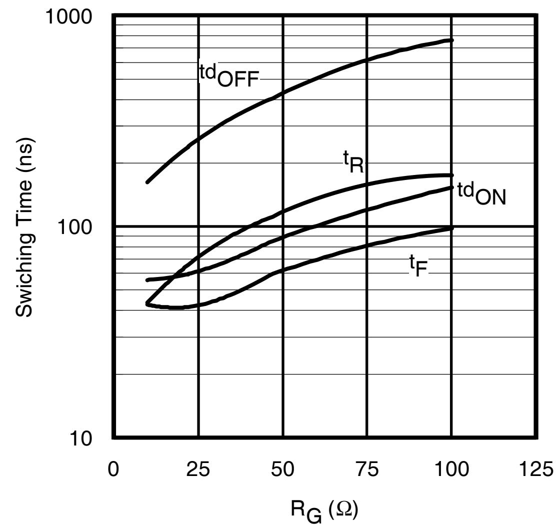


Fig. 16 - Typ. Switching Time vs. R_G
$T_J = 175°C$; $L = 200µH$; $V_{CE} = 400V$, $I_{CE} = 48A$; $V_{GE} = 15V$

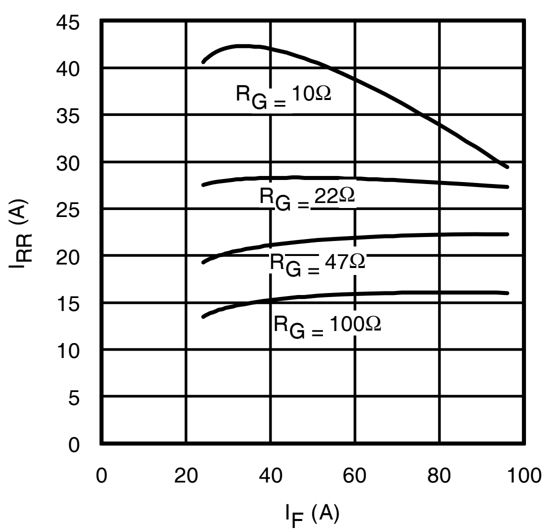


Fig. 17 - Typ. Diode I_{RR} vs. I_F
$T_J = 175°C$

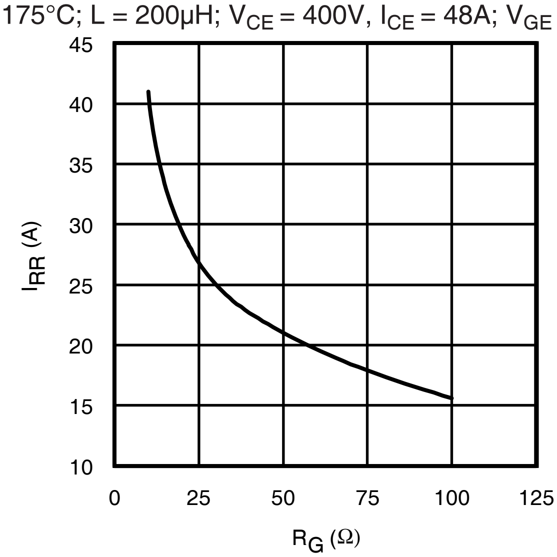


Fig. 18 - Typ. Diode I_{RR} vs. R_G
$T_J = 175°C$

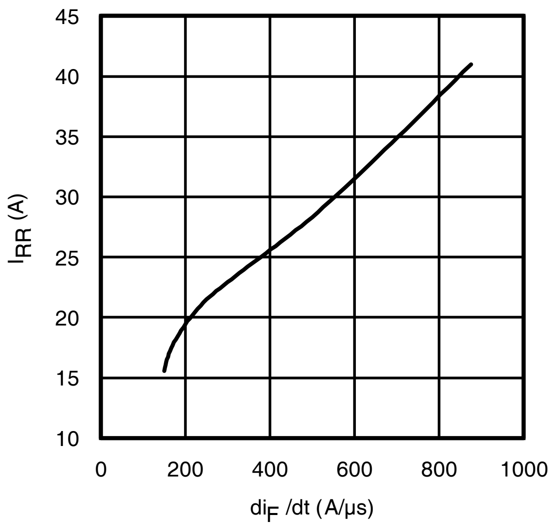


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; I_F = 48A; T_J = 175°C

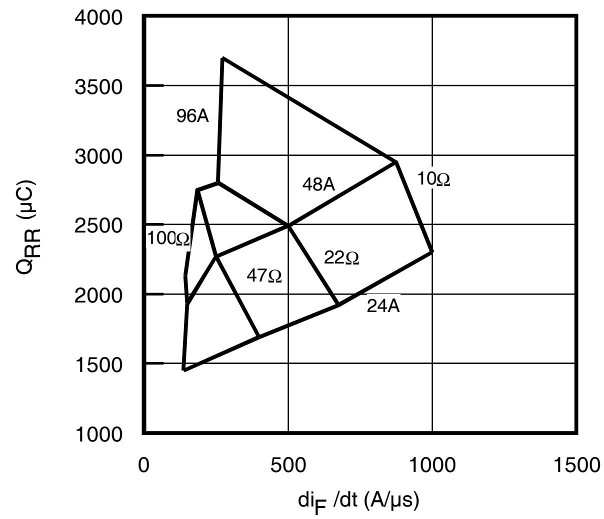


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; T_J = 175°C

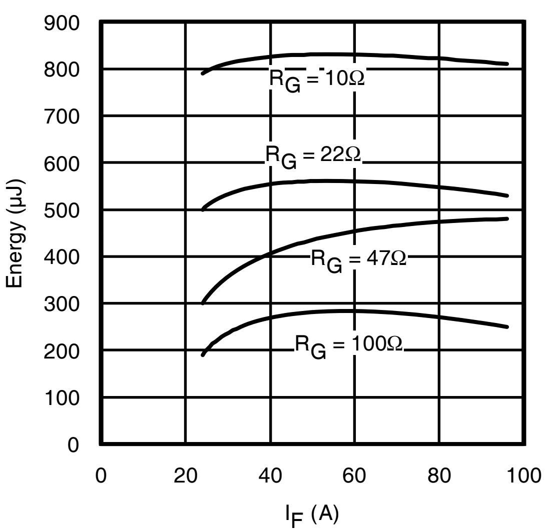


Fig. 21 - Typ. Diode E_{RR} vs. I_F
T_J = 175°C

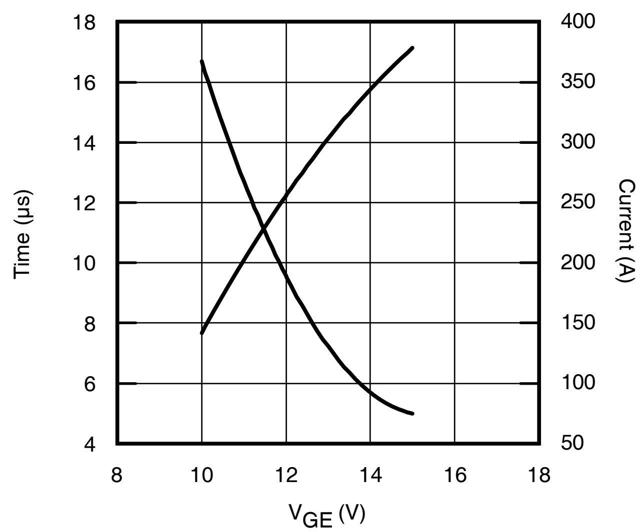


Fig. 22 - V_{GE} vs. Short Circuit Time
V_{CC} = 400V; T_C = 25°C

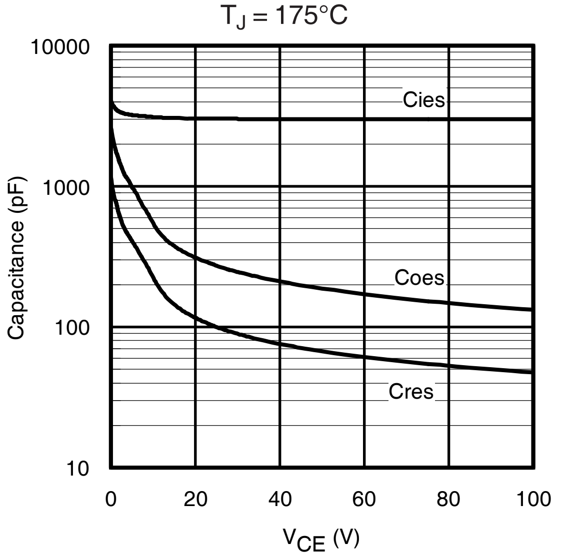


Fig. 23 - Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

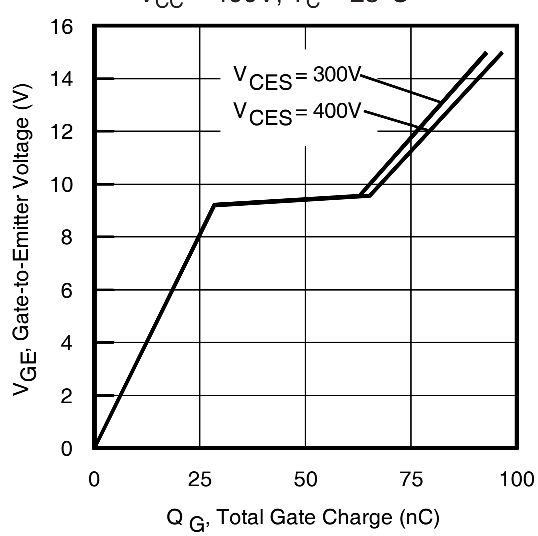
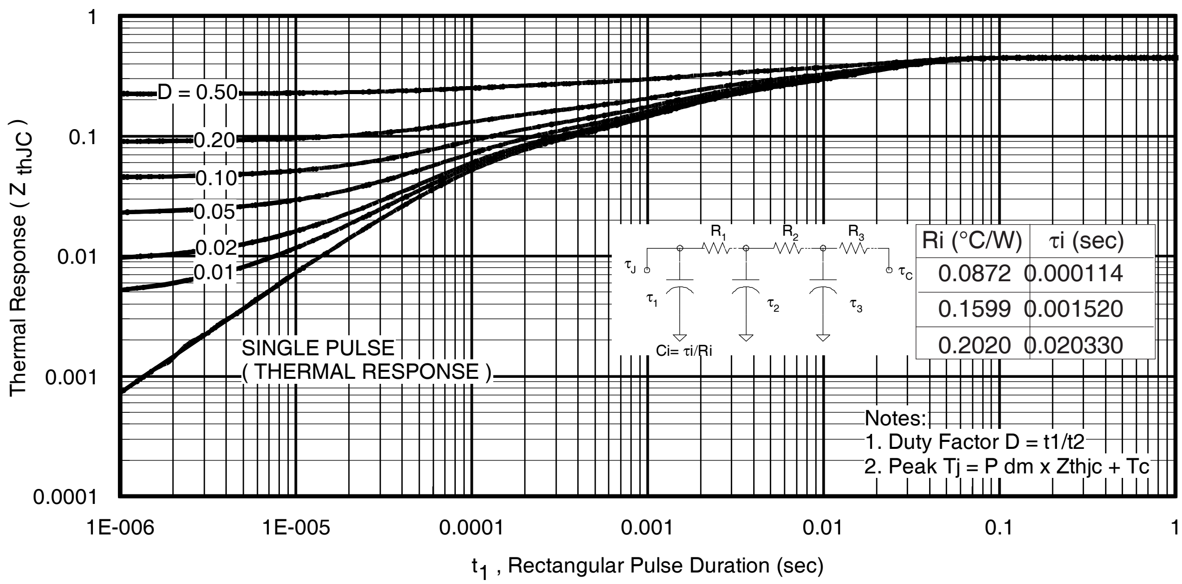
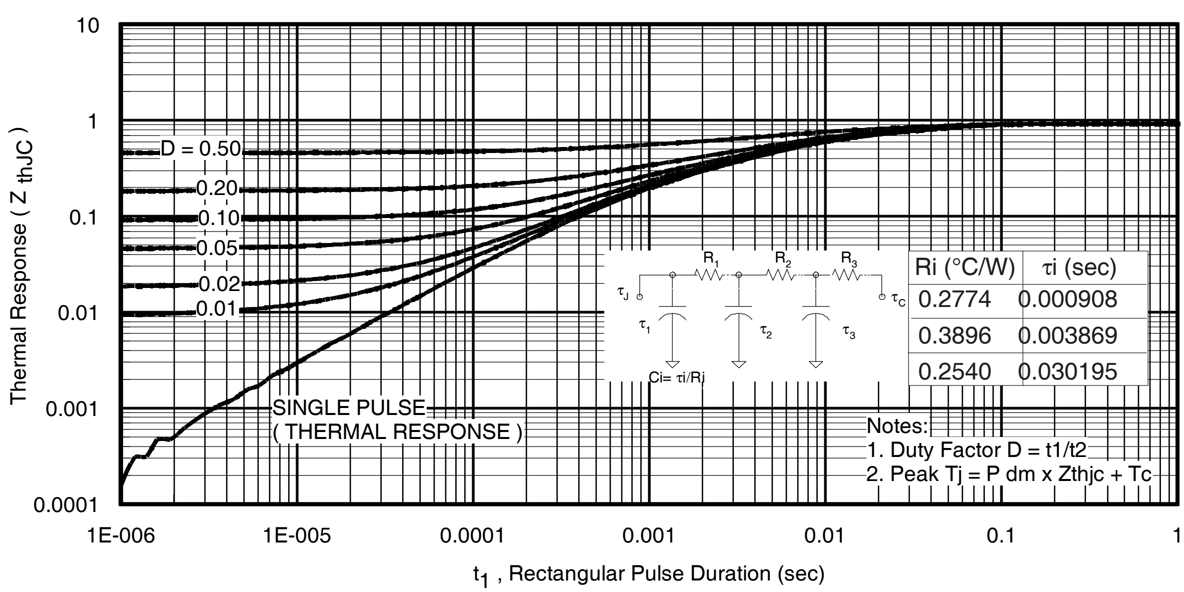


Fig. 24 - Typical Gate Charge vs. V_{GE}
I_{CE} = 48A; L = 600µH



Ri (°C/W)	τi (sec)
0.0872	0.000114
0.1599	0.001520
0.2020	0.020330

Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)



Ri (°C/W)	τi (sec)
0.2774	0.000908
0.3896	0.003869
0.2540	0.030195

Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

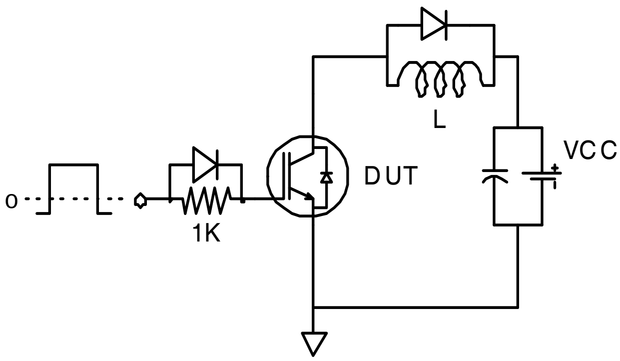


Fig.C.T.1 - Gate Charge Circuit (turn-off)

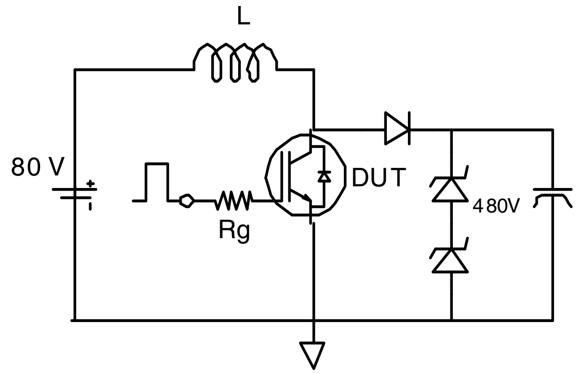


Fig.C.T.2 - RBSOA Circuit

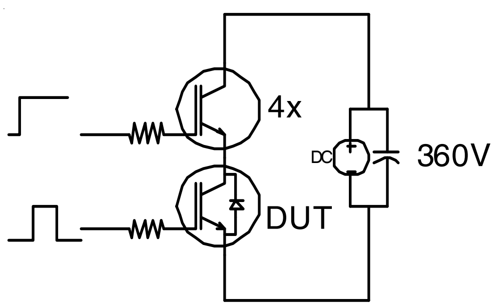


Fig.C.T.3 - S.C. SOA Circuit

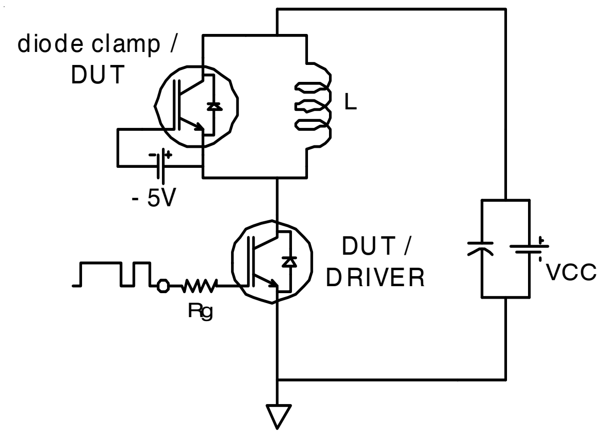


Fig.C.T.4 - Switching Loss Circuit

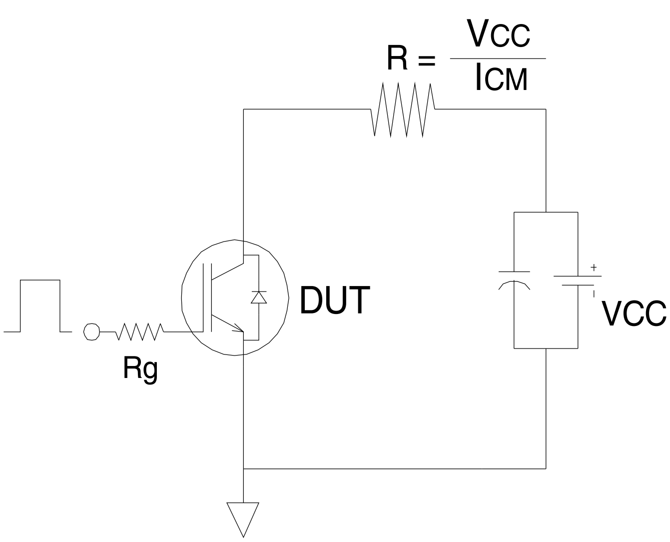


Fig.C.T.5 - Resistive Load Circuit

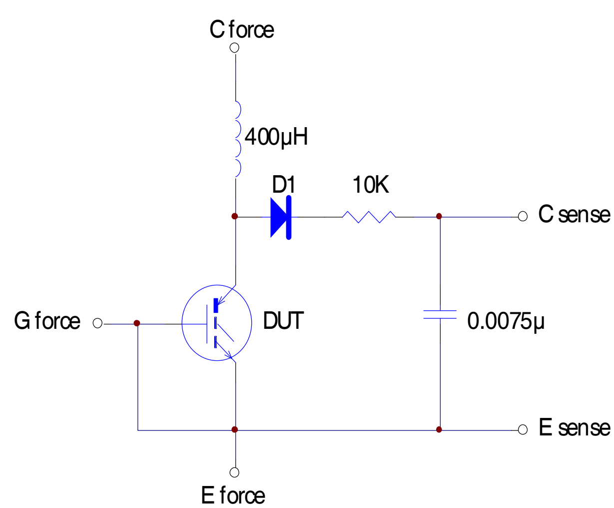


Fig.C.T.6 - BVCES Filter Circuit

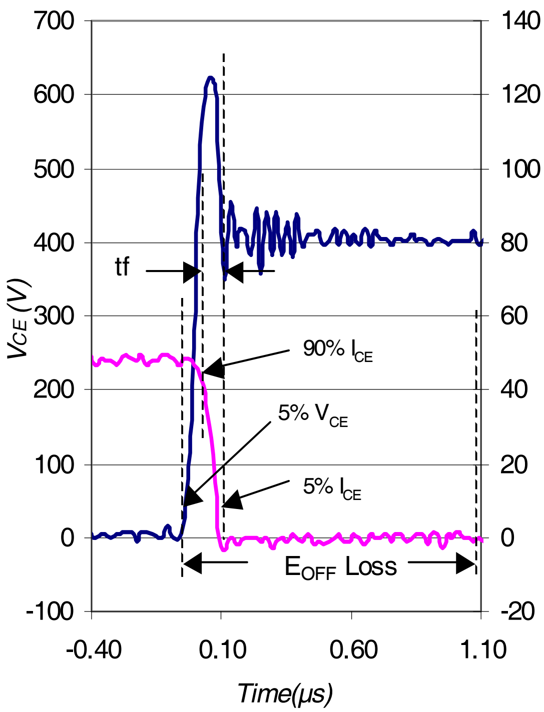


Fig. WF1 - Typ. Turn-off Loss Waveform
@ T_J = 175°C using Fig. CT.4

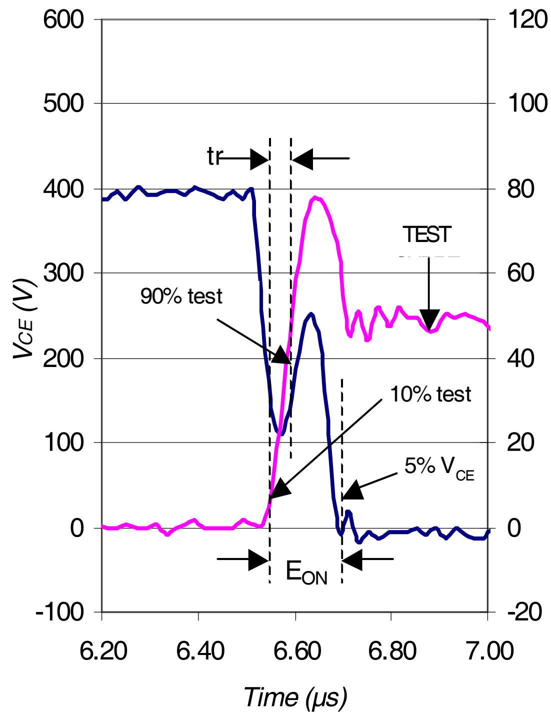


Fig. WF2 - Typ. Turn-on Loss Waveform
@ T_J = 175°C using Fig. CT.4

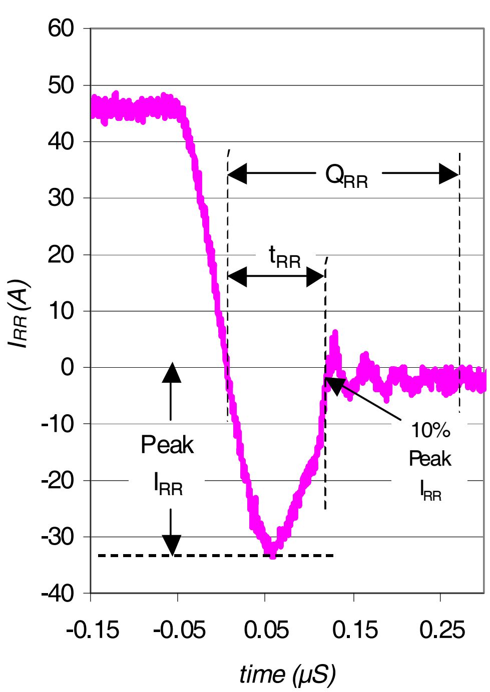


Fig. WF3 - Typ. Diode Recovery Waveform
@ T_J = 175°C using Fig. CT.4

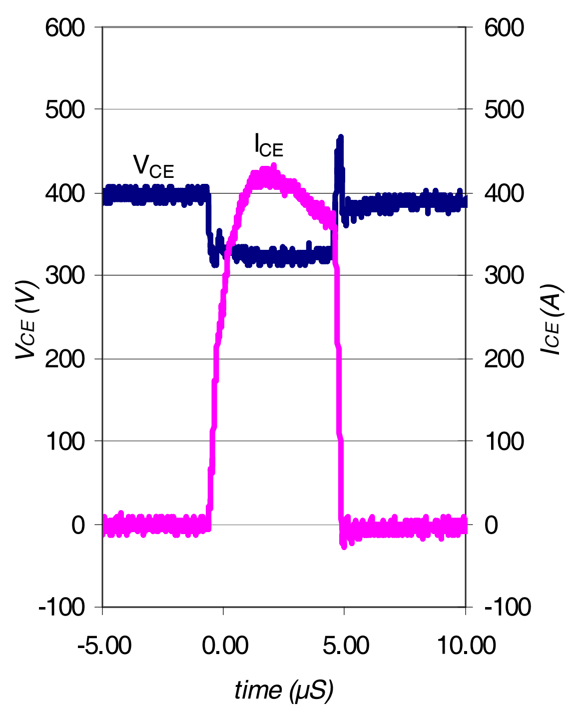
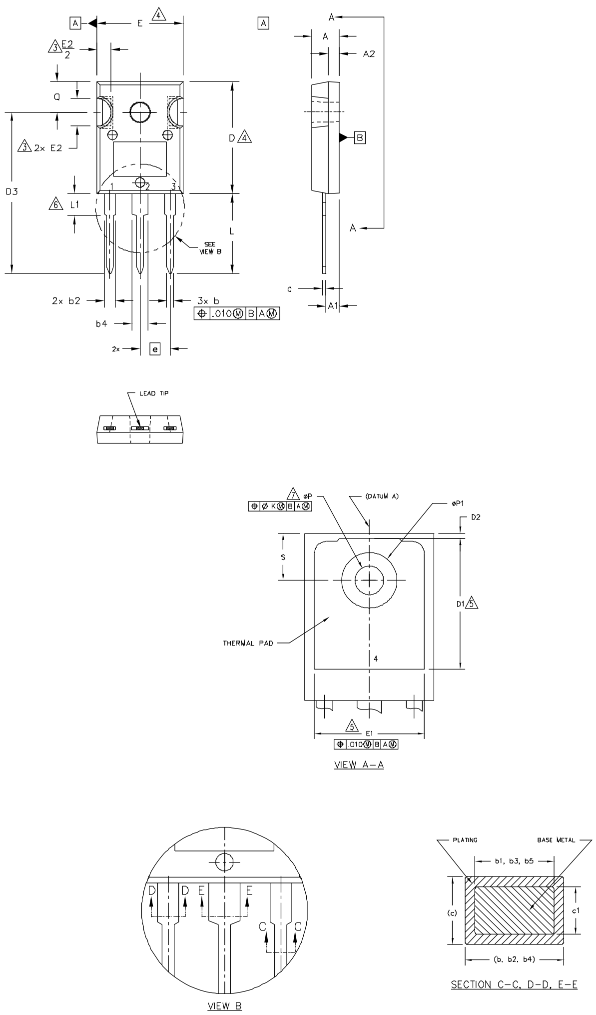


Fig. WF4 - Typ. S.C. Waveform
@ T_J = 25°C using Fig. CT.3

TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AC .

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
D3	1.122	1.161	28.50	29.50	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

SPECIAL NOTE:

a) ADDED D3 FOR SPECIAL REQUIREMENT

PART NUMBERS AFFECTED:

AUIRG4PH50S
AUIRGP4066D1/E
AUIRGP4063D/E
AUIRGP50B60PD1/E
AUIRGP35B60PD/E
AUIRGP4062D1/E
AUIRGP65A20D0
AUIRGP65G20D0
AUIRGP/F66524D0
AUIRGP/F76524D0
AUIRGP/F66548D0
AUIRGP/F76548D0

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

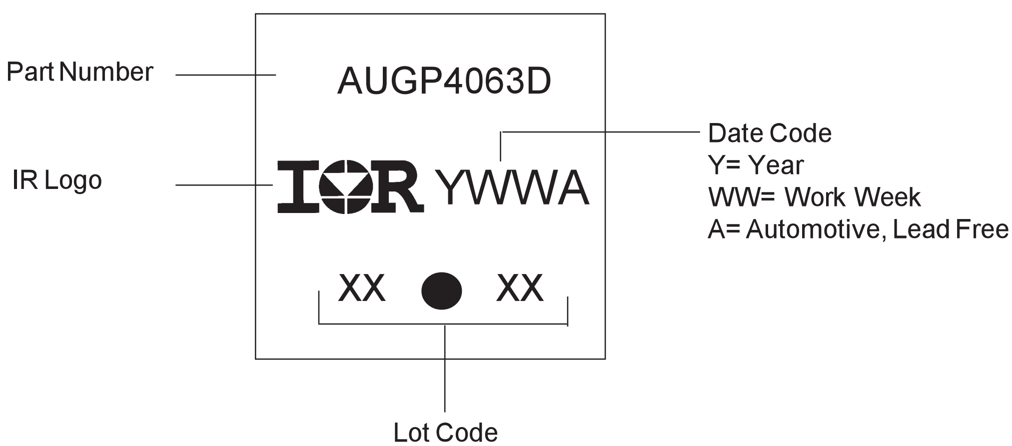
IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

DIODES

1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-247AC Part Marking Information

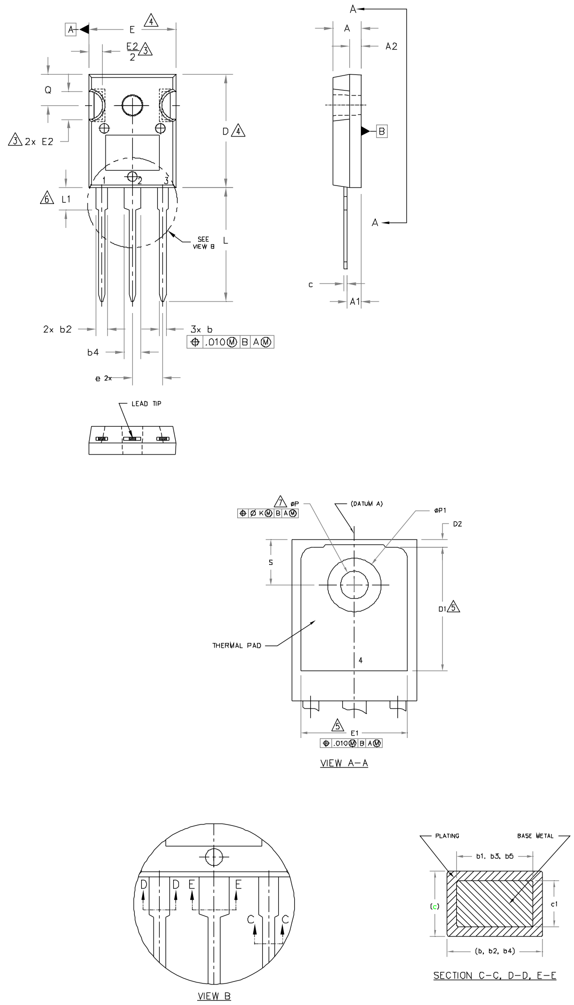


TO-247AC package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. (△) CONTOUR OF SLOT OPTIONAL.
4. (△) DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. (△) THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. (△) LEAD FINISH UNCONTROLLED IN L1.
7. (△) øP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS INCHES MIN.	INCHES MAX.	MILLIMETERS MIN.	MILLIMETERS MAX.	NOTES
A	.190	.203	4.83	5.13	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	–	13.08	–	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	–	13.46	–	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
øP	.140	.144	3.56	3.66	
øP1	–	.291	–	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

1.– GATE
2.– DRAIN
3.– SOURCE
4.– DRAIN

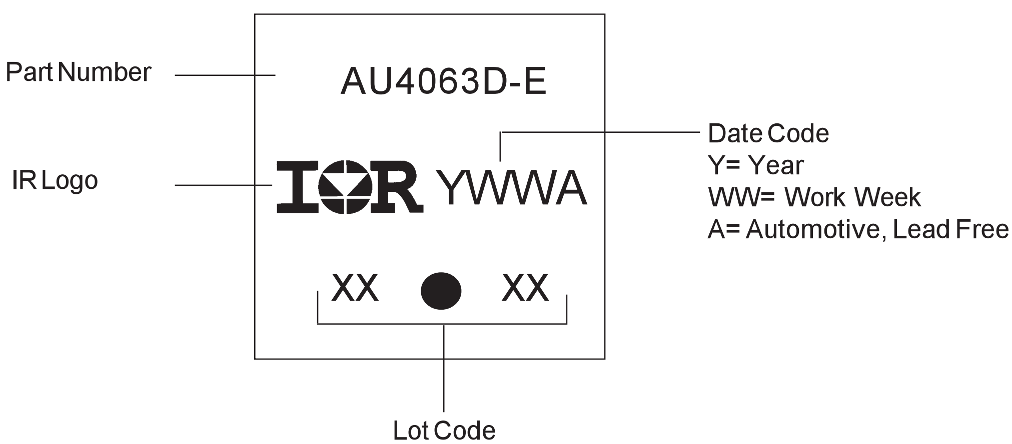
IGBTs, CoPACK

1.– GATE
2.– COLLECTOR
3.– EMITTER
4.– COLLECTOR

DIODES

1.– ANODE/OPEN
2.– CATHODE
3.– ANODE

TO-247AD Part Marking Information



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level		Automotive (per AEC-Q101)†	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		TO-247AC	N/A
		TO-247AD	N/A
ESD	Machine Model	Class M4 (±425V)†† (per AEC-Q101-002)	
	Human Body Model	Class H2 (±4000V)†† (per AEC-Q101-001)	
	Charged Device Model	Class C5 (±1125V)†† (per AEC-Q101-005)	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: http://www.irf.com

†† Highest passing voltage.

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For technical support, please contact IR's Technical Assistance Center

http://www.irf.com/technical-info/

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